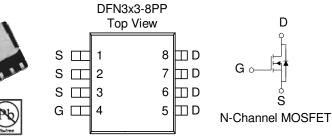
N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low $r_{DS(on)}$ provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe DFN3x3-8PP saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$			
20	9 @ $V_{GS} = 4.5V$	17			
30	11 @ $V_{GS} = 2.5V$	15			



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			30	V		
Gate-Source Voltage	V_{GS}	±8	V			
Continuous Drain Current ^a	$T_A=25^{\circ}C$	Τ_	±17			
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	ъ	±12	Α		
Pulsed Drain Current ^b	I_{DM}	±40				
Continuous Source Current (Diode Conduction) ^a	I_S	2	A			
	T _A =25°C	D	3.5	337		
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	P_{D}	2	W		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C			

HALOGEN FREE

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{ heta JC}$	25	°C/W		
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{ heta JA}$	50	°C/W		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM7336N

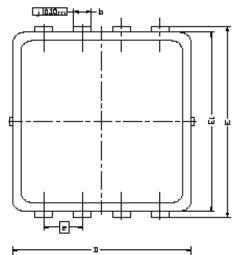
SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Domanaskan	Carrelle o I	Total Conditions	Limits			T I 4	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1		3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate voltage Diani Curient	IDSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current ^A	I _{D(on)}	$V_{\rm DS} = 5 \text{ V}, V_{\rm GS} = 10 \text{ V}$	20			A	
D i G G D i A	_	$V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A}$			9	0	
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 2 \text{ A}$			11.0	mΩ	
Forward Tranconductance ^A	gfs	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}$		40		S	
Diode Forward Voltage	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic ^b							
Total Gate Charge	Qg	V 15 V V 45 V		11			
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 10 \text{ A}$		6		nC	
Gate-Drain Charge	Qgd	ID – 10 A		4			
Input Capacitance	Ciss	N 15NN ON 6		1302			
Output Capacitance	Coss	= 1MHz		423		pF	
Reverse Transfer Capacitance	Crss			171			
Turn-On Delay Time	t _{d(on)}			10			
Rise Time	t _r	$V_{\rm DD} = 25 \; V, \; R_{\rm L} = 25 \; \Omega \; \; , \; {\rm Ib} = 1 \; {\rm A} , \; \; \; \; \; \; \; \; \; \; \; \; \; \; \; \; \; \;$		5		nS	
Turn-Off Delay Time	t _{d(off)}			22			
Fall-Time	t_{f}			4			

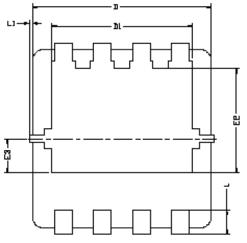
Notes

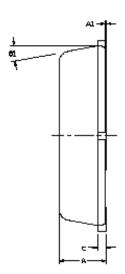
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Package Information







DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	0,700	0'80	0.900	0.0276	0.0315	0.0354
A1	0.00		0.05	0.000		0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
ר	0.10	0.152	0.25	0.004	0,006	0,010
ם	3.00 BSC			٥	118 BS	C
D1	2.35 BCC			ā.	093 BS)C
Ε	3,20 BSC			0,	126 BS	30
E1	3.00 BSC			٥	.118 BS	C
E5	1.75 BSC			a.	069 BS	ic of
E3	0.575 BSC			0.	023 BS	3C
6	0.65 BSC			Ů.	026 BS)C
L	0.30	0,40	0,50	0.0118	0.0157	0.0197
L1			0.100	D		0.004
9 1	٥°	10*	12*	0*	10°	12*